

## ABSTRACT OF THE DISCLOSURE

There is provided a protection circuit of a field effect transistor having a structure which can be fabricated without restricting a pattern layout and without increasing a process step. A protection circuit of a field effect transistor is a protection circuit of a Schottky gate HFET, and is a circuit in which a forward direction diode and a reverse direction diode are cascade-connected to form a diode unit and two such diode units are connected in series, and a gate line connected to a gate electrode of the HFET is grounded through the protection circuit. The diodes are diodes formed integrally with the Schottky gate HFET which is protected against surge breakdown, and are constituted as Schottky barrier diodes made of an  $n^+$ -GaAs cap layer formed on a GaAs substrate and Schottky electrodes formed on the  $n^+$ -GaAs cap layer.

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